

IN THE SPECIFICATION

Page 13, line 23, please delete "5 mm," and replace with "0.5 mm,".

IN THE CLAIMS

All claims pending after this amendment are listed below. Please amend the claims as follows:

Please cancel claims 1-13 and 22-32.

14. (Amended) In a chamber for processing a semiconductor wafer through plasma etching operations, the chamber including a support chuck for holding the semiconductor wafer and a pair of RF power sources; a method for making a top electrode for the chamber, comprising:

forming the top electrode to have a center region, a first surface and a second surface, the first surface has an inlet that is configured to receive processing gases from a source that is external to the system and flow the processing gases into the center region, the second surface has a plurality of gas feed holes that lead to a plurality of electrode openings that have electrode opening diameters that are greater than gas feed hole diameters of the plurality of gas feed holes, the plurality of electrode openings are configured to define the second surface which is located [an electrode surface that is defined] over a wafer surface of the semiconductor wafer.

15. The method for making a top electrode for the chamber as recited in claim 14, further comprising:

coupling the top electrode to one of the pair of RF power sources and the support chuck to the other one of the pair of RF power sources.

16. (Amended) The method for making a top electrode for the chamber as recited in claim 15, further comprising:

forming the electrode openings to be at least about [5] 0.5 mm or greater in diameter and the gas feed holes to have a diameter of about [1] 0.1 mm.

17. The method for making a top electrode for the chamber as recited in claim 15, further comprising:

defining the electrode openings to a depth of between about 1/32 inch and 1/4 inch.

18. The method for making a top electrode for the chamber as recited in claim 16, further comprising:

fixing a separation of between about 0.75 cm and about 4 cm between the electrode surface and the wafer surface.

19. The method for making a top electrode for the chamber as recited in claim 18, further comprising:

inserting two or more gas buffer plates within the center region of the top electrode.